

SOT-23 Plastic-Encapsulate Transistors

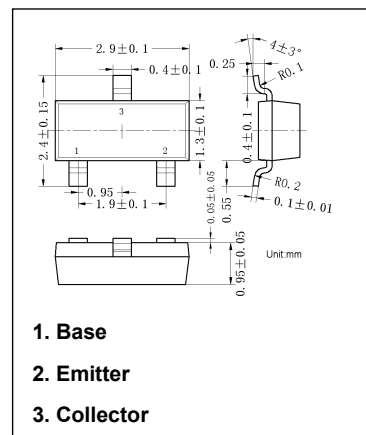
BC856A PNP Transistors

Features

- Ideally suited for automatic insertion
- For switching and AF amplifier applications

Marking

- BC856A: 3A
- BC856B: 3B



Maximum Ratings (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector Base Voltage	-80	V
V _{CEO}	Collector Emitter Voltage	-65	V
V _{EBO}	Emitter Base Voltage	-5	V
I _c	Collector Current	-0.1	A
P _c	Collector Power Dissipation	200	mW
R _{θJA}	Thermal Resistance from Junction to Ambient	625	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	- 55 to +150	°C

Electrical Characteristics (T_a=25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _{(BR)CBO}	Collector-base breakdown voltage	I _C = -10μA, I _E = 0	-80			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = -10mA, I _B = 0	-65			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E = -1μA, I _C = 0	-5			V
I _{CBO}	Collector cut-off current	V _{CB} = -70V, I _E = 0			-100	nA
I _{CEO}	Collector cut-off current	V _{CE} = -60V, I _B = 0			-100	nA
I _{EBO}	Emitter cut-off current	V _{EB} = -5V, I _C = 0			-100	nA
h _{FE}	DC current gain	BC856A V _{CE} = -5V, I _C = -2mA	125		250	
		BC856B V _{CE} = -5V, I _C = -2mA	220		475	
		V _{CE} = -5V, I _C = -1mA	125			
V _{CE(sat)}	Collector-emitter saturation voltage	I _C = -100mA, I _B = -5mA			-0.5	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C = -100mA, I _B = -5mA			-1.1	V
f _T	Transition frequency	V _{CE} = -5V, I _C = -10mA, f = 100MHz	100			MHz
C _{ob}	Collector output capacitance	V _{CB} = -10V, f = 1MHz			4.5	pF

Typical Characteristics

